

Deep Gap Slotted Optical Switch Type OPB815L

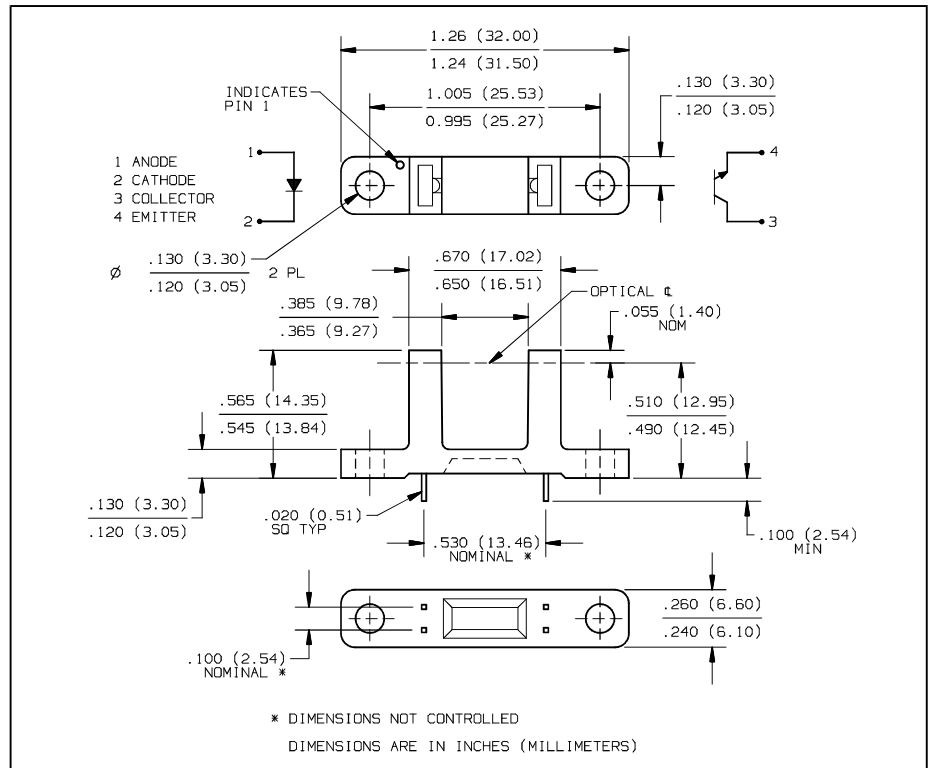


Features

- Non-contact switching
- Printed circuit board mounting
- 0.375" (9.53 mm) wide slot
- 0.430" (10.92 mm) deep slot

Description

The OPB815L consists of an infrared emitting diode and an NPN silicon phototransistor mounted in a low cost plastic housing on opposite sides of a 0.375" (9.53 mm) wide, 0.430" (10.92 mm) deep slot. Phototransistor switching takes place whenever an opaque object passes through the slot. Available with wire leads as OPB815W.



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Storage and Operating Temperature	-40° C to +85° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	240° C ⁽¹⁾
Input Diode	
Continuous Forward Current	50 mA
Peak Forward Current (1 μs pulse width, 300 pps)	3.0 A
Reverse Voltage	2.0 V
Power Dissipation	100 mW ⁽²⁾

Output Phototransistor

Collector-Emitter Voltage	30 V
Emitter-Collector Voltage	5.0 V
Power Dissipation	100 mW ⁽²⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max when flow soldering.
- (2) Derate linearly 1.67 mW/ $^\circ\text{C}$ above 25° C.
- (3) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.
- (4) All parameters tested using pulse technique.

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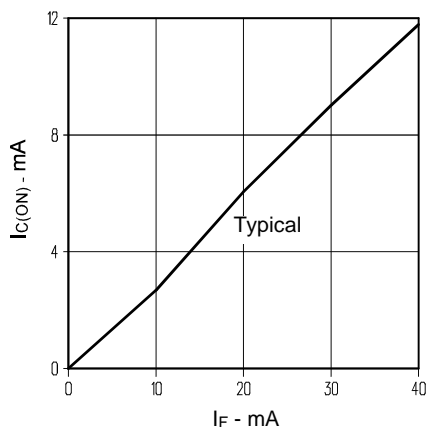
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Input Diode					
V_F	Forward Voltage		1.70	V	$I_F = 20\text{ mA}$
I_R	Reverse Current		100	μA	$V_R = 2.0\text{ V}$
Output Phototransistor					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	30		V	$I_C = 1.00\text{ mA}$
$V_{(BR)ECO}$	Emitter-Collector Breakdown Voltage	5.0		V	$I_E = 100\ \mu\text{A}$
I_{CEO}	Collector-Emitter Dark Current		100	nA	$V_{CE} = 10.0\text{ V}, I_F = 0, E_e = 0$
Coupled					
$V_{CE(SAT)}$	Collector-Emitter Saturation Voltage		0.40	V	$I_C = 500\ \mu\text{A}, I_F = 20\text{ mA}$
$I_{C(ON)}$	On-State Collector Current	3.5	16.0	mA	$V_{CE} = 10.0\text{ V}, I_F = 20\text{ mA}$

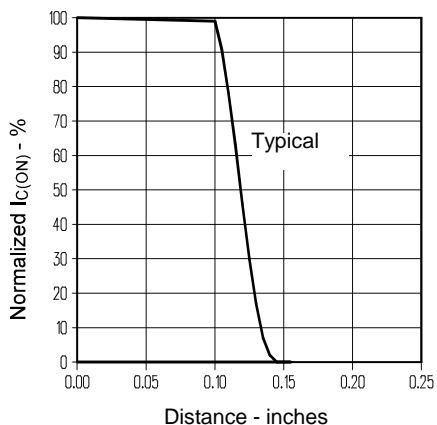
SLOTTED OPTICAL COMPONENTS

Typical Performance Curves

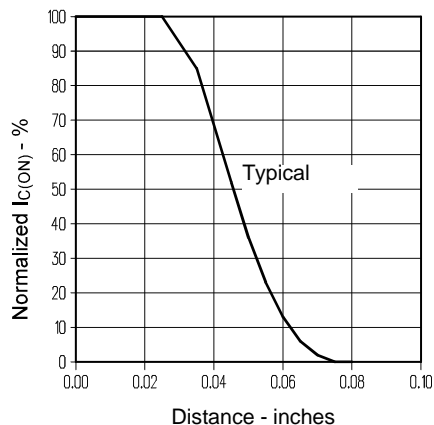
Collector Current vs LED Drive



Normalized $I_{C(ON)}$ vs Distance (X Axis Blocked)



Normalized $I_{C(ON)}$ vs Distance (Y Axis Blocked)



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible

Optek Technology, Inc. 1215 W. Crosby Road Carrollton, Texas 75006 (972)323-2200 Fax (972)323-2396